



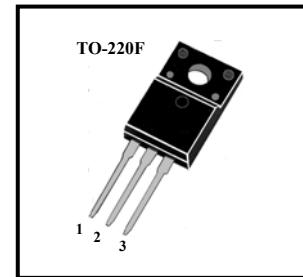
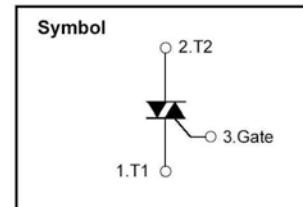
Shantou Huashan Electronic Devices Co.,Ltd.

HBT139F-600

INSULATED TYPE TRIAC (TO-220F PACKAGE)

■ Features

- * Repetitive Peak Off-State Voltage: 600V
- * R.M.S On-State Current($I_{T(RMS)}=16A$)
- * High Commutation dv/dt
- * Isolation Voltage ($V_{ISO}=1500V$ AC)



■ General Description

This device is fully isolated package suitable for AC switching application, phase control application such as fan speed and temperature modulation control, lighting control and static switching relay.

■ Absolute Maximum Ratings ($T_a=25^\circ C$)

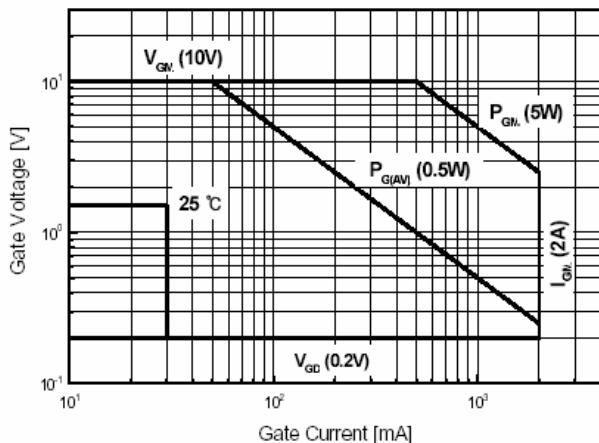
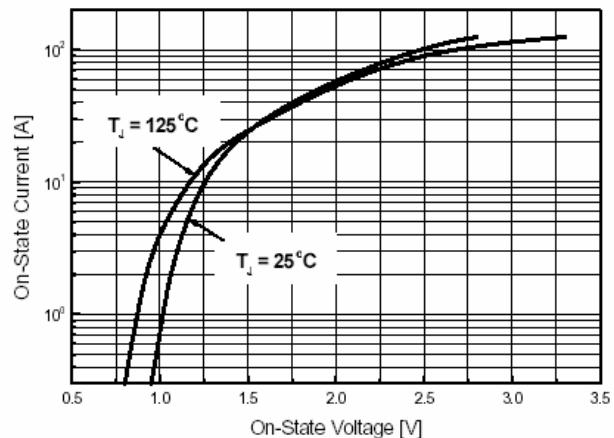
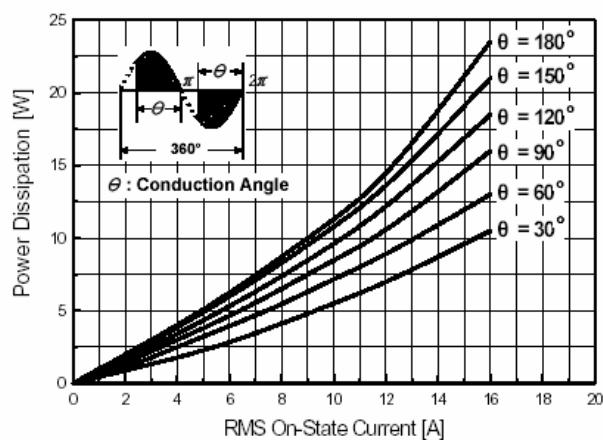
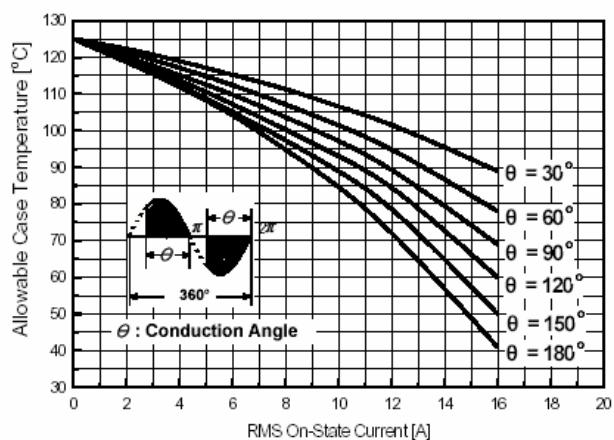
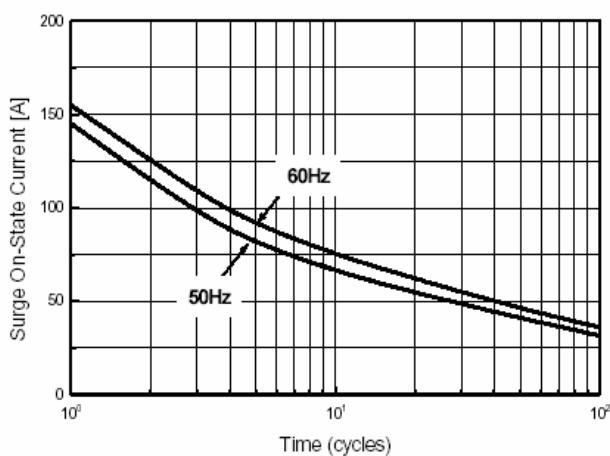
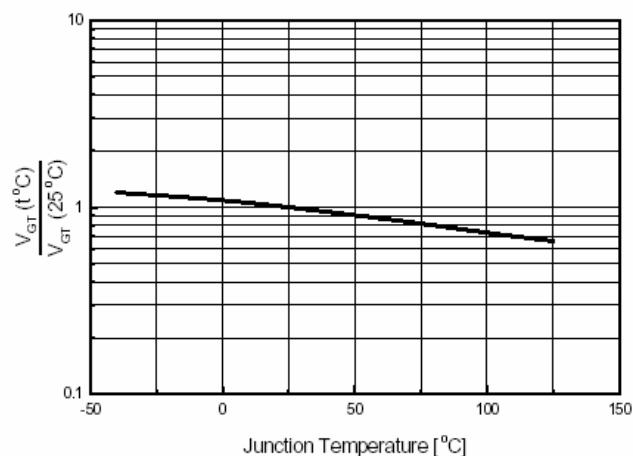
T_{stg} — Storage Temperature	-40~150°C
T_j — Operating Junction Temperature	-40~125°C
P_{GM} — Peak Gate Power Dissipation	5W
V_{DRM} — Repetitive Peak Off-State Voltage	600V
I_T (RMS) — R.M.S On-State Current ($T_c=41^\circ C$)	16A
V_{GM} — Peak Gate Voltage	10V
I_{GM} — Peak Gate Current	2.0A
I_{TSM} — Surge On-State Current (One Cycle, 50/60Hz,Peak,Non-Repetitive)	145/155A
V_{ISO} — Isolation Breakdown Voltage (R.M.S, A.C.1minute)	1500V

■ Electrical Characteristics ($T_a=25^\circ C$)

Symbol	Items	Min		Max	Unit	Conditions
I_{DRM}	Repetitive Peak Off-State Current			2.0	mA	$V_D=V_{DRM}$, Single Phase, Half Wave, $T_j=125^\circ C$
V_{TM}	Peak On-State Voltage			1.6	V	$I_T=20A$, Inst. Measurement
I_{+GT1}	Gate Trigger Current (I)			25	mA	$V_D=6V$, $R_L=10$ ohm
I_{-GT1}	Gate Trigger Current (II)			25	mA	$V_D=6V$, $R_L=10$ ohm
I_{-GT3}	Gate Trigger Current (III)			25	mA	$V_D=6V$, $R_L=10$ ohm
V_{+GT1}	Gate Trigger Voltage (I)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{-GT1}	Gate Trigger Voltage (II)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{-GT3}	Gate Trigger Voltage (III)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{GD}	Non-Trigger Gate Voltage	0.2			V	$T_j=125^\circ C$, $V_D=1/2V_{DRM}$
$(dv/dt)_c$	Critical Rate of Rise of Off-State Voltage at Commutation	10			V/ μ s	$T_j=125^\circ C$, $V_D=2/3V_{DRM}$ $(di/dt)_c=-6A/ms$
I_H	Holding Current		20		mA	
$R_{th(j-c)}$	Thermal Resistance			3.5	°C/W	Junction to case



■ Performance Curves

Fig 1. Gate Characteristics**Fig 2. On-State Voltage****Fig 3. On State Current vs.
Maximum Power Dissipation****Fig 4. On State Current vs.
Allowable Case Temperature****Fig 5. Surge On-State Current Rating
(Non-Repetitive)****Fig 6. Gate Trigger Voltage vs.
Junction Temperature**



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Fig 7. Gate Trigger Current vs.
Junction Temperature

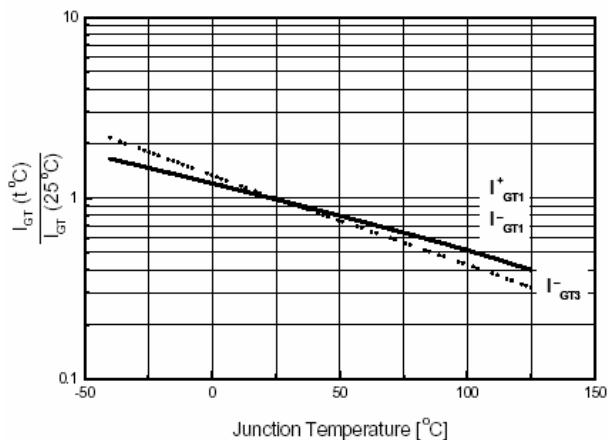


Fig 8. Transient Thermal Impedance

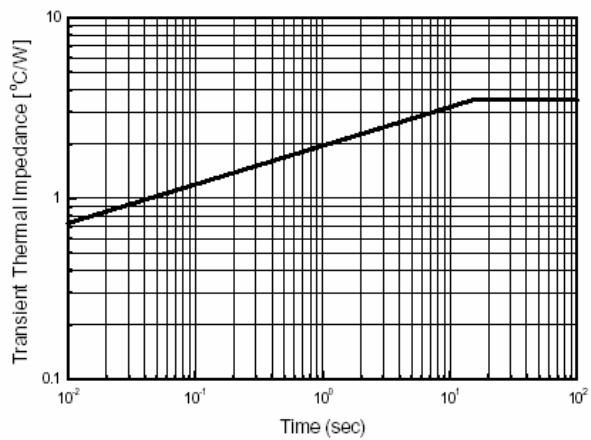
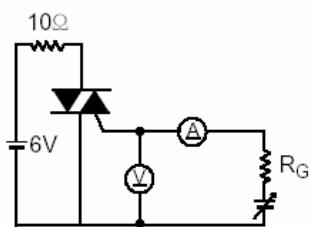
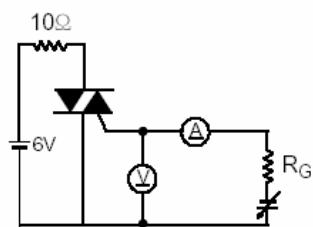


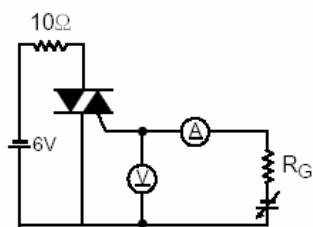
Fig 9. Gate Trigger Characteristics Test Circuit



Test Procedure I



Test Procedure II



Test Procedure III